

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C6 600V

600V CoolMOS™ C6 Power Transistor
IPU60R2K0C6

Data Sheet

Rev. 2.2
Final

Industrial & Multimarket

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom, UPS.

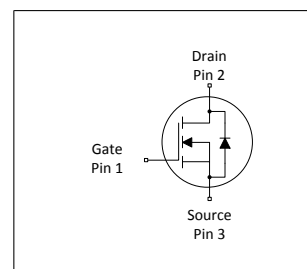
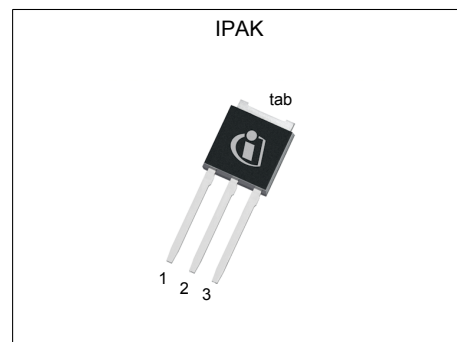


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	2	Ω
Q_g,typ	6.7	nC
$I_D,pulse$	6	A
$E_{oss} @ 400V$	0.76	μJ
Body diode di/dt	500	A/ μs

Type / Ordering Code	Package	Marking	Related Links
IPU60R2K0C6	PG-TO 251	6R2K0C6	see Appendix A

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D			2.4	A	$T_C = 25^\circ\text{C}$
				1.5		$T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$			6	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}			11	mJ	$I_D = 0.4\text{A}$, $V_{DD} = 50\text{V}$ (see table 10)
Avalanche energy, repetitive	E_{AR}			0.06	mJ	$I_D = 0.4\text{A}$, $V_{DD} = 50\text{V}$
Avalanche current, repetitive	I_{AR}			0.4	A	
MOSFET dv/dt ruggedness	dv/dt			50	V/ns	$V_{DS} = 0 \dots 480\text{V}$
Gate source voltage	V_{GS}	-20		20	V	static
		-30		30		AC ($f > 1\text{ Hz}$)
Operating and storage temperature	T_j, T_{stg}	-55		150	$^\circ\text{C}$	
Continuous diode forward current	I_S			2.1	A	$T_C = 25^\circ\text{C}$
Diode pulse current	$I_{S,pulse}$			6	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt			15	V/ns	$V_{DS} = 0 \dots 480\text{V}$, $I_{SD} \leq I_D$, $T_j = 25^\circ\text{C}$ (see table 8)
Maximum diode commutation speed	di/dt			500	A/ μs	
Power dissipation	P_{tot}			22.3		$T_C = 25^\circ\text{C}$

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_θ

3 Thermal characteristics

Table 3 Thermal characteristics IPAK

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}			5.6	°C/W	
Thermal resistance, junction - ambient ¹⁾	R_{thJA}			62	°C/W	SMD version, device on PCB, minimal footprint
			35			SMD version, device on PCB, 6cm ² cooling area
Soldering temperature, wave- & reflowsoldering allowed	T_{sold}			260	°C	reflow MSL

¹⁾ Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

4 Electrical characteristics

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600			V	$V_{GS} = 0V, I_D = 0.25mA$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5	V	$V_{DS} = V_{GS}, I_D = 0.1mA$
Zero gate voltage drain current	I_{DSS}			1	μA	$V_{DS} = 600V, V_{GS} = 0V, T_j = 25^\circ C$
			10			$V_{DS} = 600V, V_{GS} = 0V, T_j = 150^\circ C$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS} = 20V, V_{DS} = 0V$
Drain-source on-state resistance	$R_{DS(on)}$		1.800	2	Ω	$V_{GS} = 10V, I_D = 0.8A, T_j = 25^\circ C$
			4.680			$V_{GS} = 10V, I_D = 0.76A, T_j = 150^\circ C$
Gate resistance	R_G		12		Ω	$f = 1MHz$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}		140		pF	$V_{GS} = 0V, V_{DS} = 100V, f = 1MHz$
Output capacitance	C_{oss}		12		pF	
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$		8.5		pF	$V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$		30		pF	$I_D = \text{constant}, V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Turn-on delay time	$t_{d(on)}$		7		ns	$V_{DD} = 400V, V_{GS} = 10V, I_D = 0.9A, R_G = 12.2\Omega$ (see table 9)
Rise time	t_r		7		ns	
Turn-off delay time	$t_{d(off)}$		30		ns	
Fall time	t_f		50		ns	

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}		0.8		nC	$V_{DD} = 480V, I_D = 0.9A, V_{GS} = 0 \text{ to } 10V$
Gate to drain charge	Q_{gd}		3.6		nC	
Gate charge total	Q_g		6.7		nC	
Gate plateau voltage	$V_{plateau}$		5.4		V	

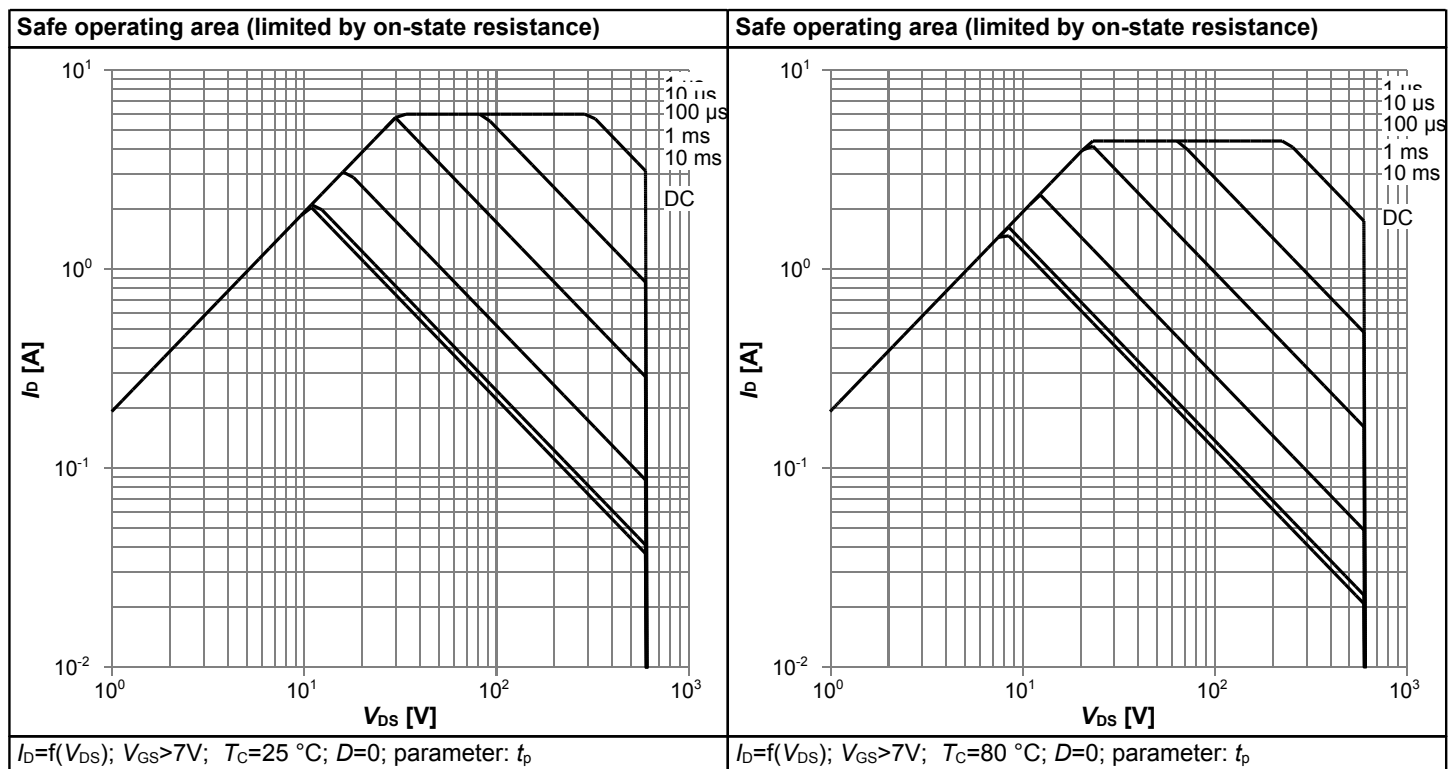
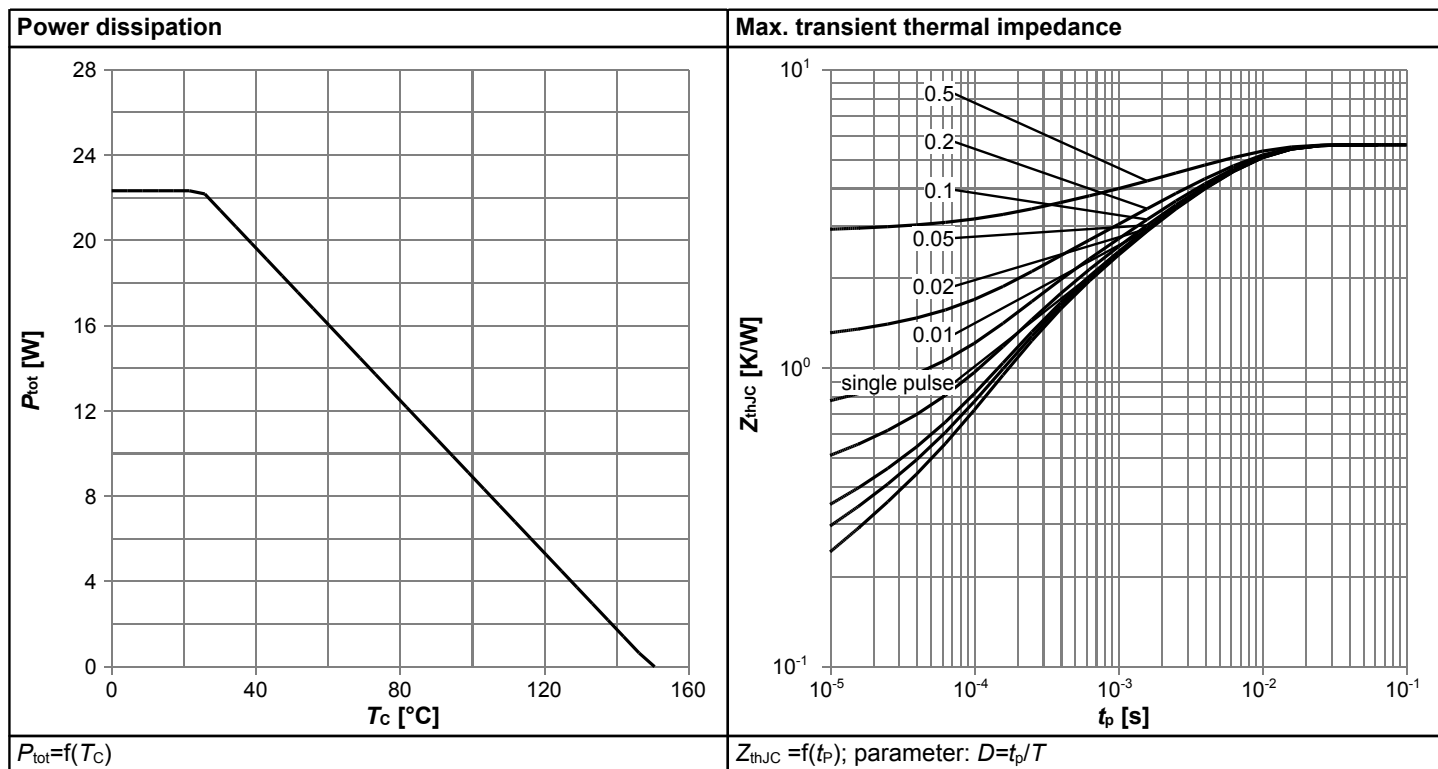
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

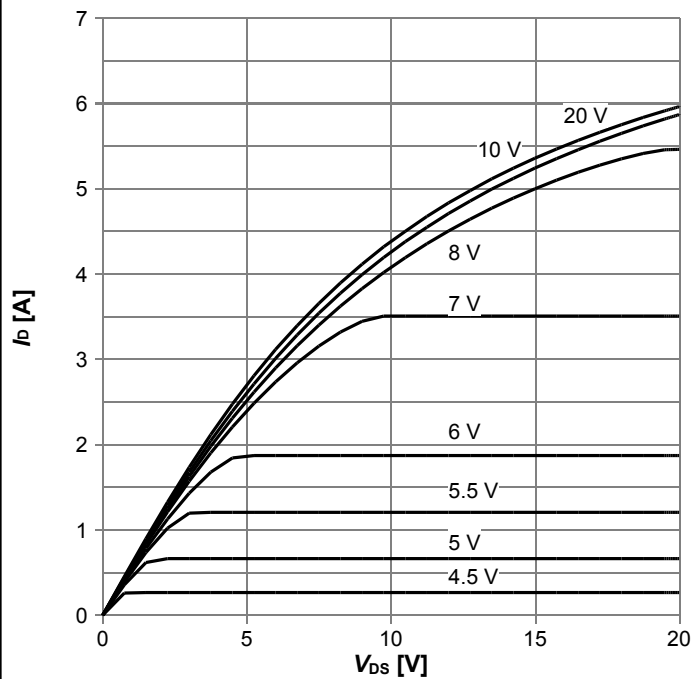
Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}		0.9		V	$V_{GS} = 0V$, $I_F = 0.9A$, $T_J = 25^\circ C$
Reverse recovery time	t_{rr}		180		ns	$V_R = 400V$, $I_F = 0.9A$, $di_F/dt = 100A/\mu s$ (see table 8)
Reverse recovery charge	Q_{rr}		0.67		μC	
Peak reverse recovery current	I_{rrm}		7.1		A	

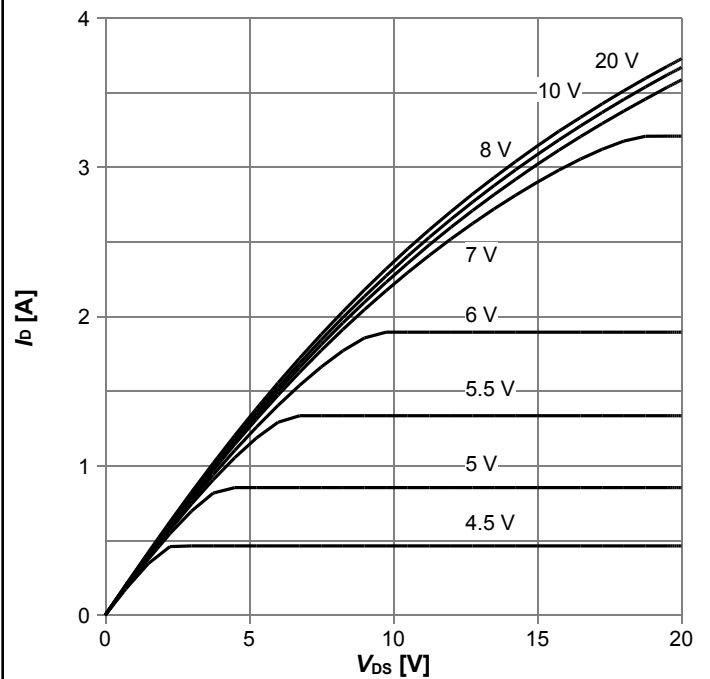
5 Electrical characteristics diagrams



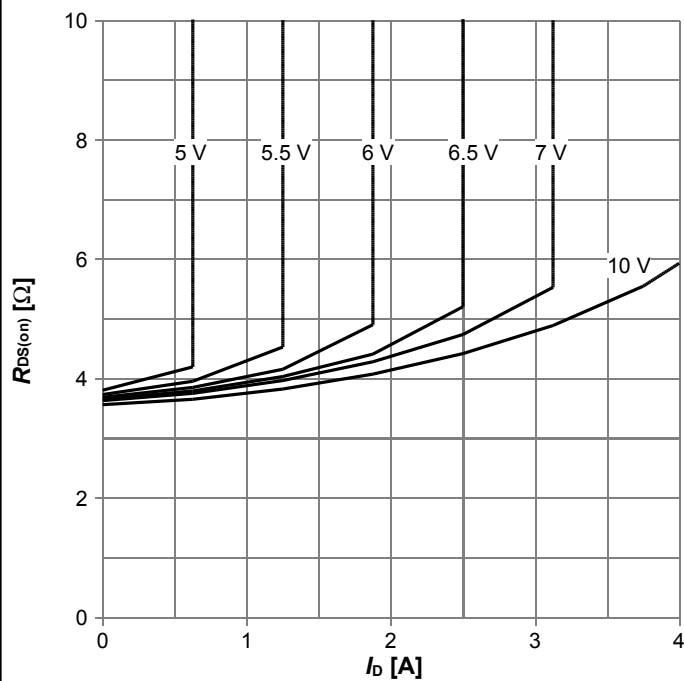
Typ. output characteristics


 $I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

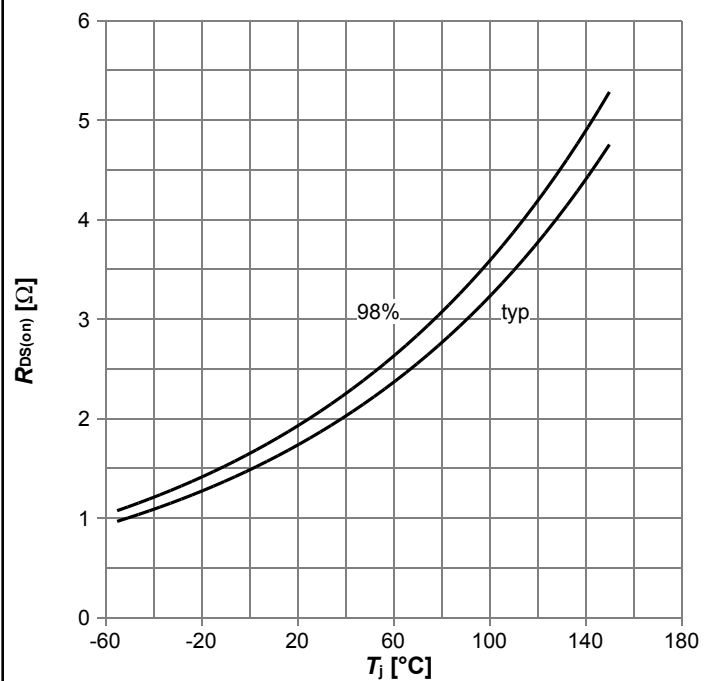
Typ. output characteristics

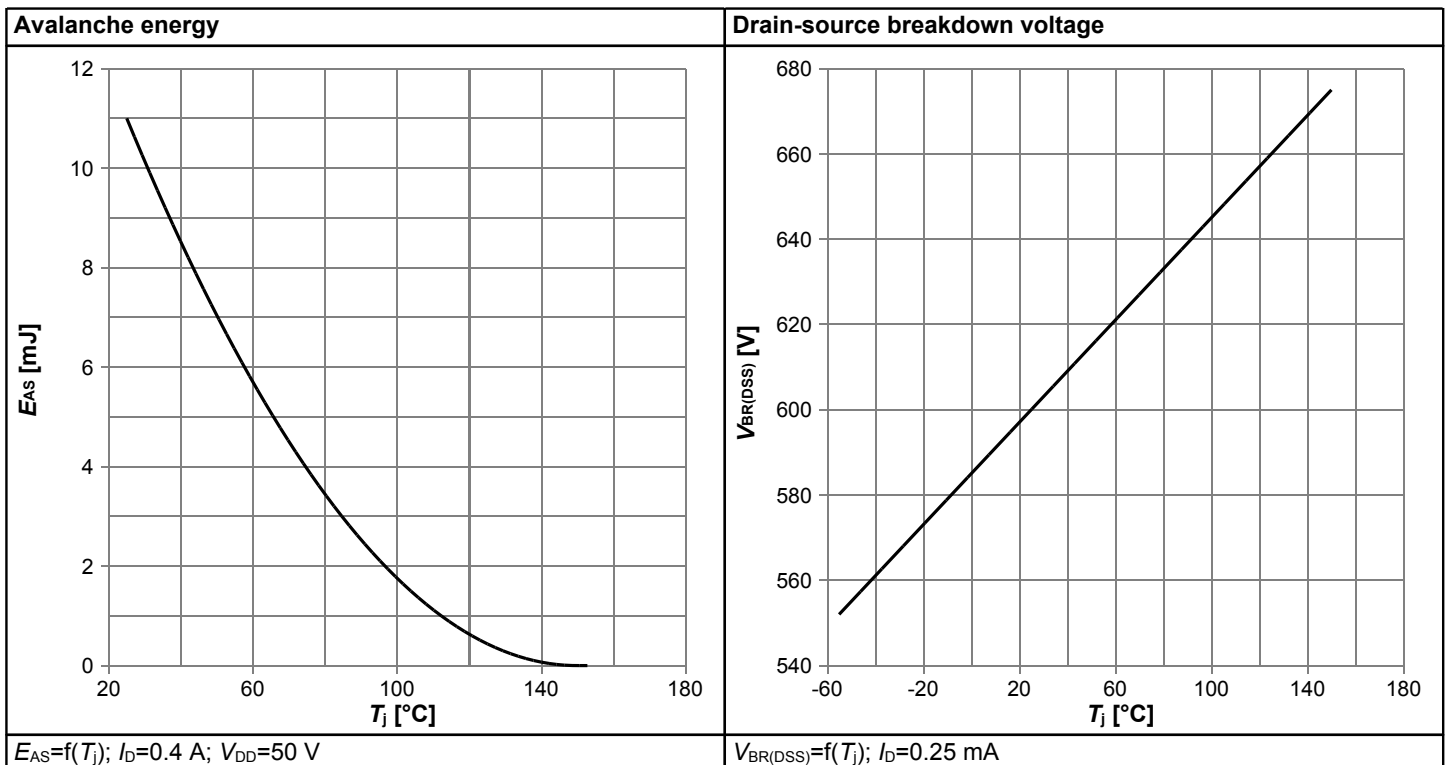
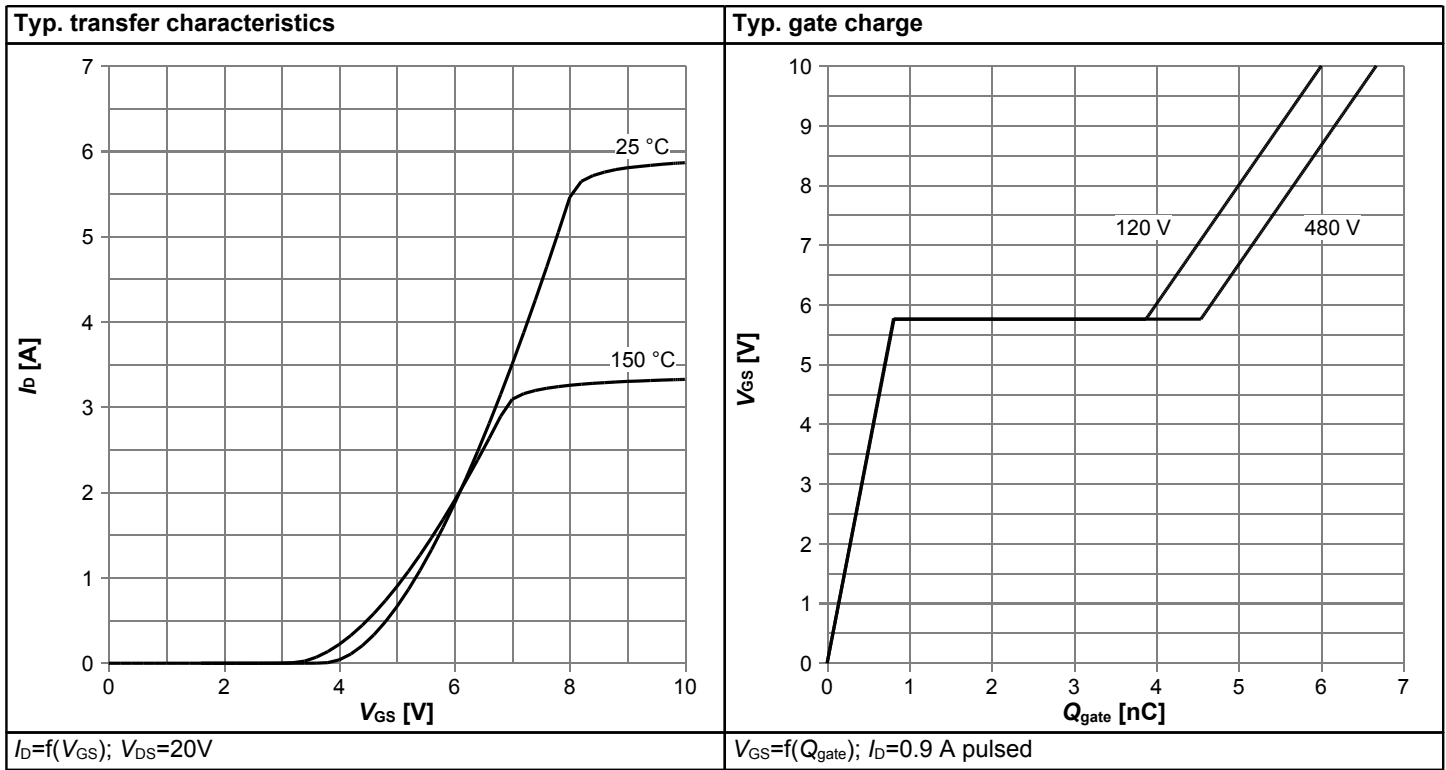

 $I_D = f(V_{DS})$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Typ. drain-source on-state resistance

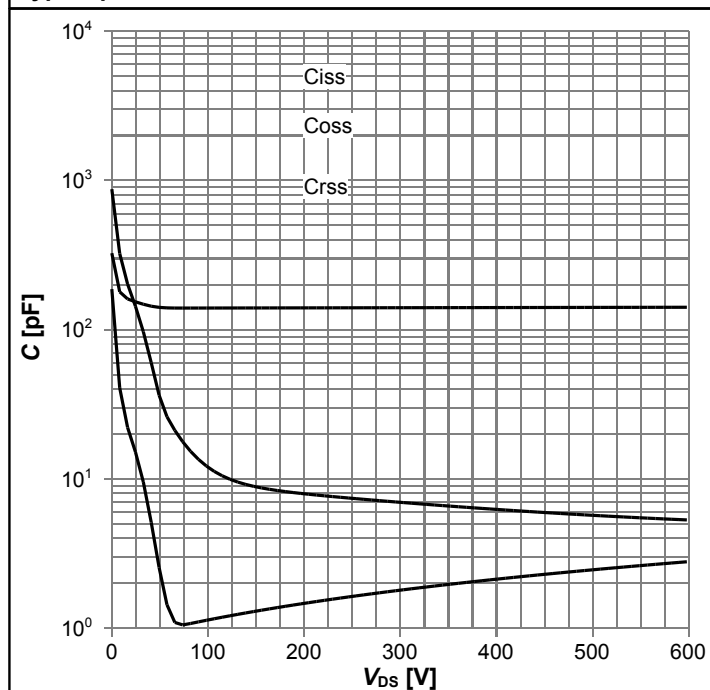

 $R_{DS(on)} = f(I_D)$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Drain-source on-state resistance

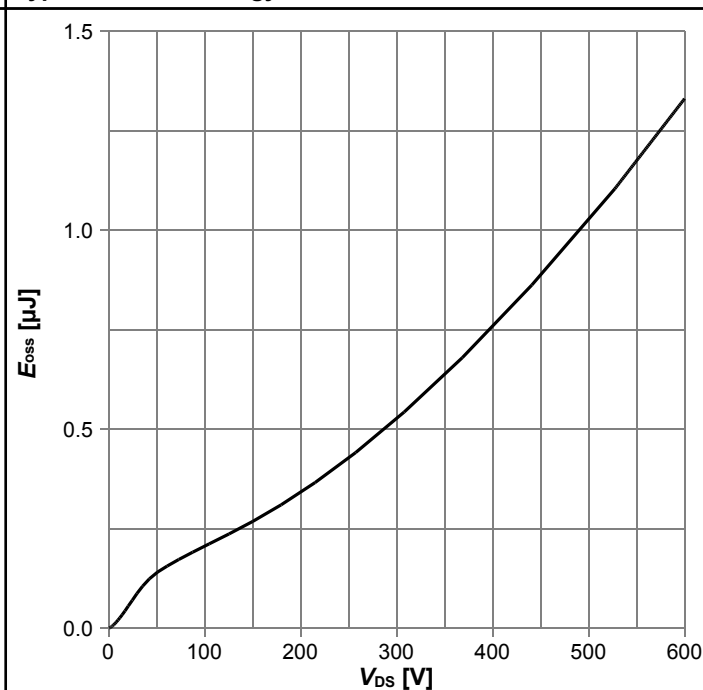

 $R_{DS(on)} = f(T_j)$; $I_D = 0.76\text{ A}$; $V_{GS} = 10\text{ V}$



Typ. capacitances

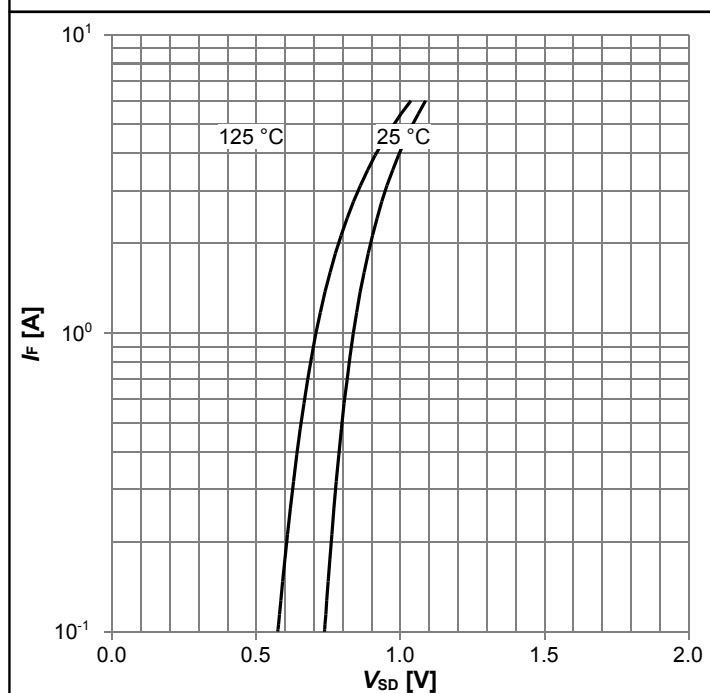


$$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$$

Typ. C_{OSS} stored energy


$$E_{OSS}=f(V_{DS})$$

Forward characteristics of reverse diode



$$I_F=f(V_{SD}); \text{parameter: } T_j$$

6 Test Circuits

Table 8 Diode characteristics

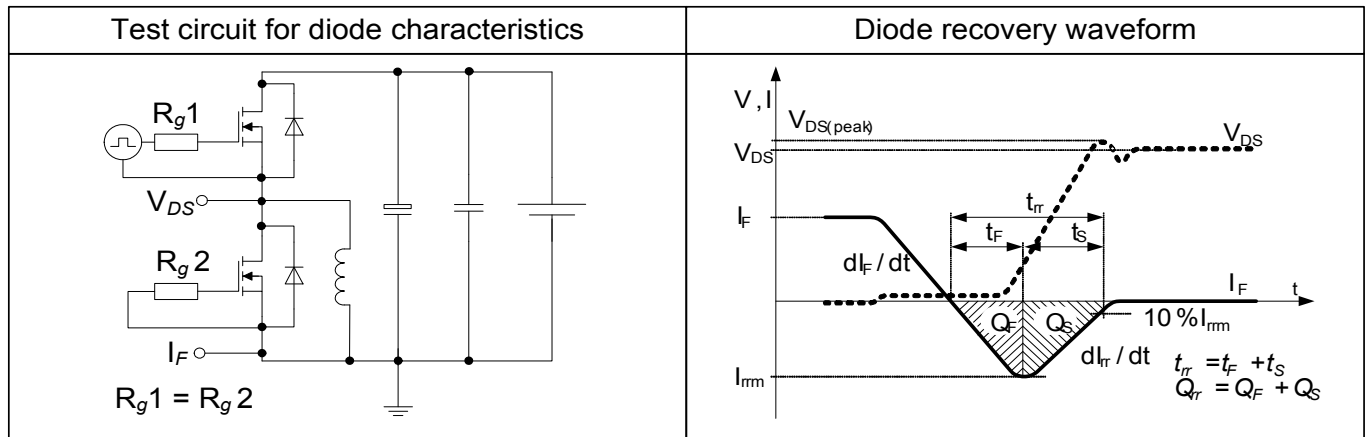


Table 9 Switching times

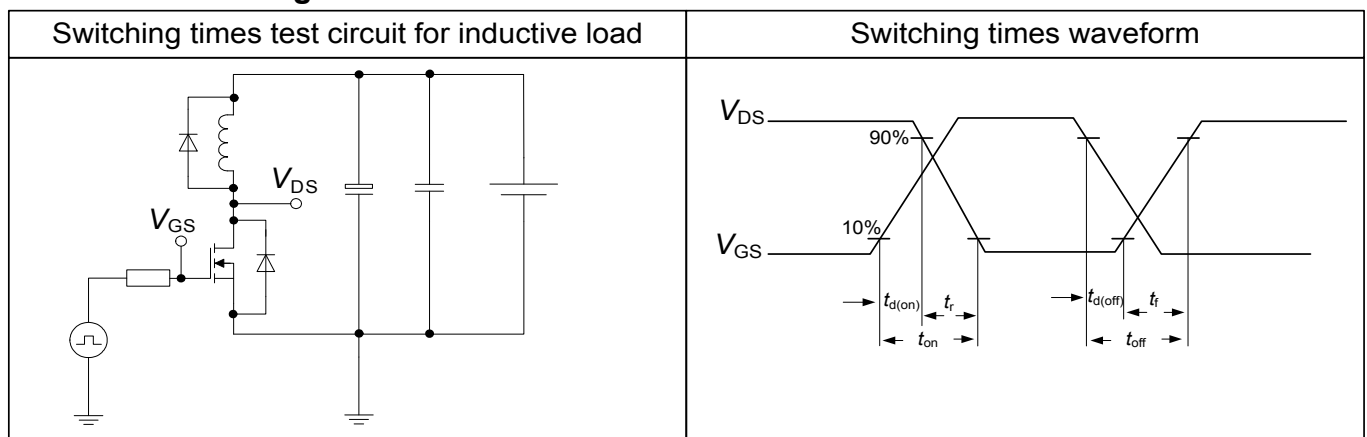
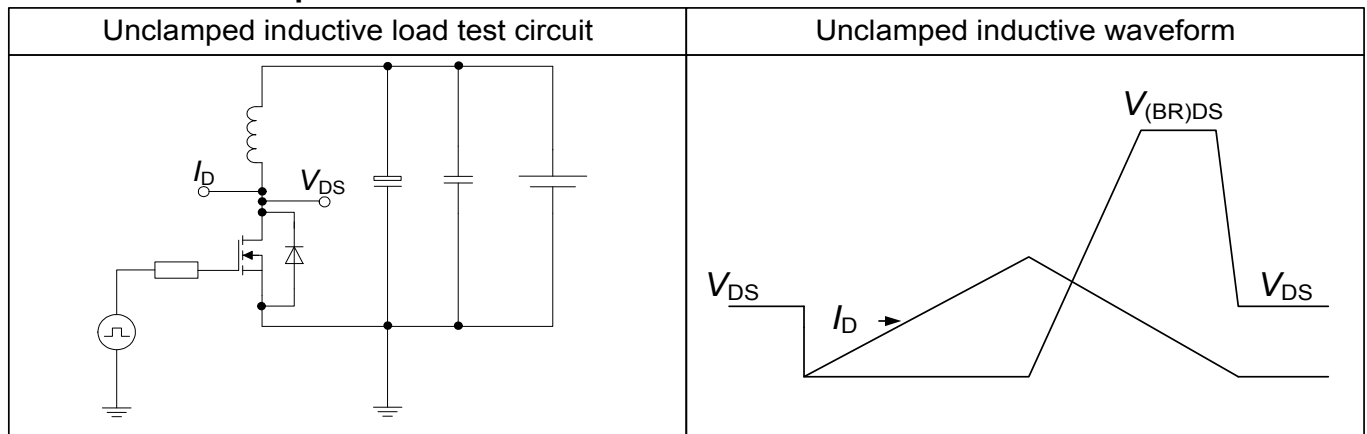
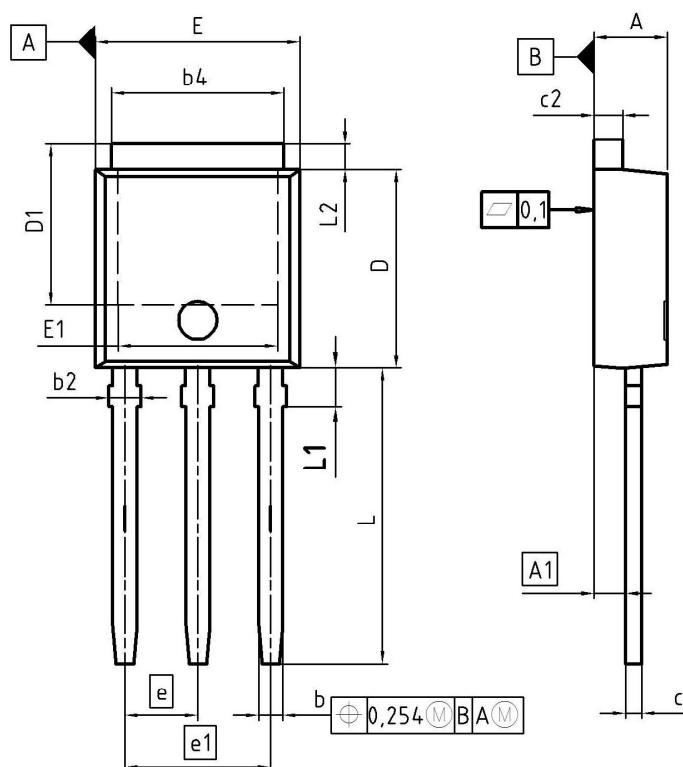


Table 10 Unclamped inductive load



7 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.90	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.77	0.198	0.227
E	6.35	6.73	0.250	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	8.89	9.65	0.350	0.380
L1	1.90	2.29	0.075	0.090
L2	0.89	1.37	0.035	0.054

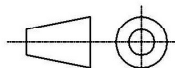
DOCUMENT NO. Z8B00003330
SCALE 0 2.0 4mm
EUROPEAN PROJECTION 
ISSUE DATE 19-03-2008
REVISION 03

Figure 1 Outline PG-TO 251, dimensions in mm/inches

8 Appendix A

Table 11 Related Links

- **IFX C6 Product Brief:** www.infineon.com
- **IFX C6 Portfolio:** www.infineon.com
- **IFX CoolMOS Webpage:** www.infineon.com
- **IFX Design Tools:** www.infineon.com

Revision History

IPU60R2K0C6

Revision: 2015-10-09, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2012-02-02	Final datasheet release
2.2	2015-10-09	Updated with Halogen free information

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